imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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SOT-23



Pin Definition:

1. Gate 2. Source 3. Drain

Key Parameter Performance

Parameter		Value	Unit	
V _{DS}		-30	V	
	$V_{GS} = -10V$	95	mΩ	
$R_{DS(on)}(max)$	$V_{GS} = -4.5V$	140		
Q _g		10	nC	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing		
TSM2307CX RFG	SOT-23	3kpcs / 7" Reel		

Note: "G" denotes for Halogen- and Antimony-free as those which contain

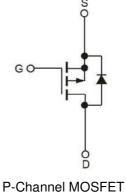
<900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds

Absolute Maximum Ratings ($T_c = 25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current (Note 1)		I _D	-3	А	
Pulsed Drain Current (Note 2)		I _{DM}	-20	А	
Continuous Source Current (Diode Conduction)		I _S	-1.7	А	
Power Dissipation	$T_a = 25^{\circ}C$	5	1.25	W	
	$T_a = 75^{\circ}C$	P _D	0.8		
Operating Junction Temperature		TJ	+150	°C	
Storage Temperature Range		T _{STG}	-50 to +150	°C	

Block Diagram





Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R _{eJC}	75	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	130	°C/W

Electrical Specifications (T_c = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250 \mu A$	BV _{DSS}	-30			V
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -3A$	D		76	95	mΩ
	$V_{GS} = -4.5V, I_D = -2A$	R _{DS(ON)}		103	140	mΩ
Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, \ I_{\text{D}} = -250 \mu A$	V _{GS(TH)}	-1		-3	V
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
Gate Body Leakage	$V_{GS} = \pm 20V, \ V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance (Note 4)	$V_{DS} = -10V, I_{D} = -6A$	g _{fs}		5		S
Diode Forward Voltage	$I_{\rm S} = -1.7 V, V_{\rm GS} = 0 V$	V _{SD}			-1.2	V
Dynamic						
Total Gate Charge (Note 3,4)		Qg		10	15	nC
Gate-Source Charge (Note 3,4)	$V_{DS} = -15V, I_D = -3A,$	Q _{gs}		1.9		
Gate-Drain Charge (Note 3,4)	$-V_{GS} = -10V$	Q_gd		2		
Input Capacitance		C _{iss}		565		
Output Capacitance	$V_{DS} = -30V, V_{GS} = 0V,$	C _{oss}		126		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		75		
Switching					•	
Turn-On Delay Time (Note 3,4))		t _{d(on)}		10	20	
Turn-On Rise Time (Note 3,4)	$V_{DD} = -15V, R_L = 15\Omega,$ $I_D = -1A, V_{GEN} = -10V,$	t _r		9	20	
Turn-Off Delay Time (Note 3,4)		t _{d(off)}		27	50	ns
Turn-Off Fall Time (Note 3,4)	$-R_{\rm G}=6\Omega$	t _f		7	16	1

Note:

1.Limited by maximum junction temperature

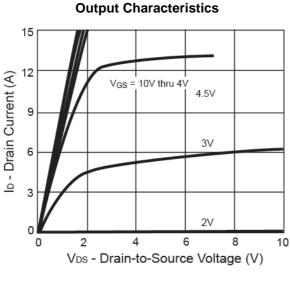
2. Pulse width limited by safe operating area

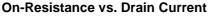
3.Pulse test: pulse width \leq 300µs, duty cycle \leq 2%

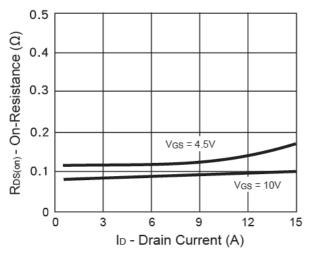
4.Switching time is essentially independent of operating temperature.



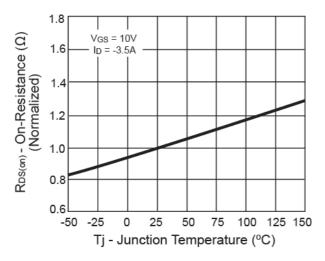
Electrical Characteristics Curve

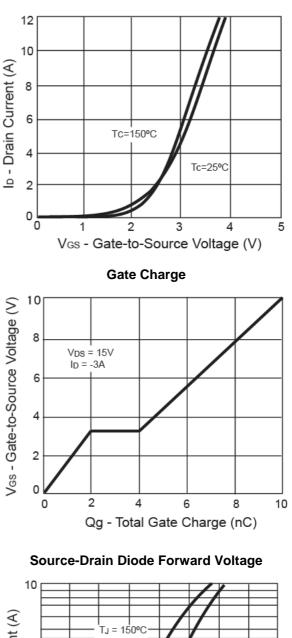




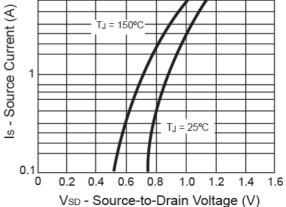








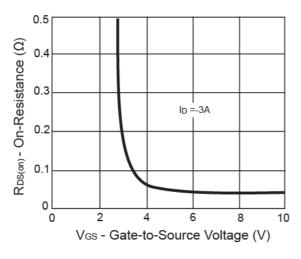
Transfer Characteristics



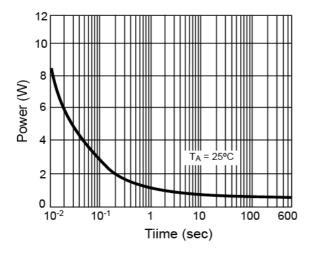


Electrical Characteristics Curve

On-Resistance vs. Gate-Source Voltage



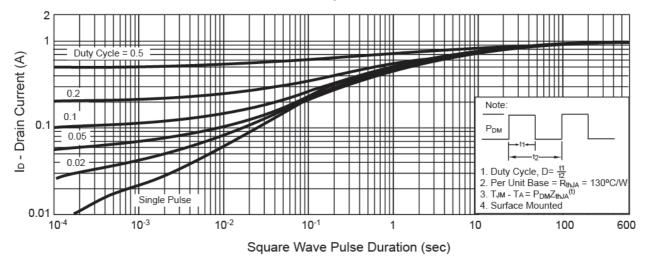
Single Pulse Power



0.3 0.2 V_{GS(th)} - Variance (V) $I_{D} = 250 uA$ 0.1 -0.0 -0.1 -0.2 -0.3 -50 125 150 -25 0 25 50 75 100 Tj - Junction Temperature (°C)

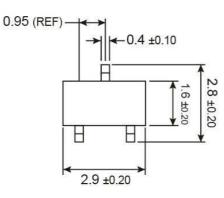
Threshold Voltage

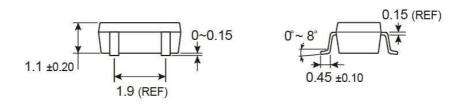
Normalized Thermal Transient Impedance, Junction-to-Ambient





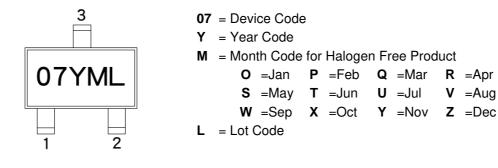
SOT-23 Mechanical Drawing





Unit: Millimeters

Marking Diagram







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